

ABSTRACT

5 A tungsten sintered compact sputtering target, wherein a molybdenum strength detected with a secondary ion mass spectrometer (D-SIMS) is equal to or less than 1/10000 of the tungsten strength. This invention aims to reduce the specific resistance of a tungsten film sputtered using the tungsten sintered compact target by reducing the molybdenum in the tungsten sintered compact sputtering target and adjusting the grain size distribution of the W powder that is used during sintering.

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Fig. 1